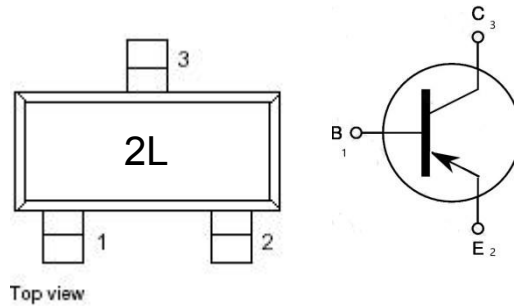


一、Features 产品特性


印字 marking: 2L

MAXIMUM RATINGS(T_a=25℃) 最大额定值

CHARACTERISTIC 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Collector-Emitter Voltage 集电极-发射极电压	V _{CEO}	-150	Vdc
Collector-Base Voltage 集电极-基极电压	V _{CBO}	-160	Vdc
Emitter-Base Voltage 发射极-基极电压	V _{EBO}	-5.0	Vdc
Collector Current 集电极电流	I _c	-500	mAdc

THERMAL CHARACTERISTICS 热特性

CHARACTERISTIC 特性参数	Symbol 符号	Max 最大值	Unit 单位
Total power dissipation 总耗散功率 (T _{amb} -25℃;note1)	P _D	225	mW
Junction and Storage Temperature 结温和储存温度	T _j , T _{stg}	150, -65~150	℃
Operating ambient temperature 工作环境温度	T _{amb}	-65~150	℃
Thermal resistance from junction to ambient 热阻(note1)	R _{th j-a}	556	K/W

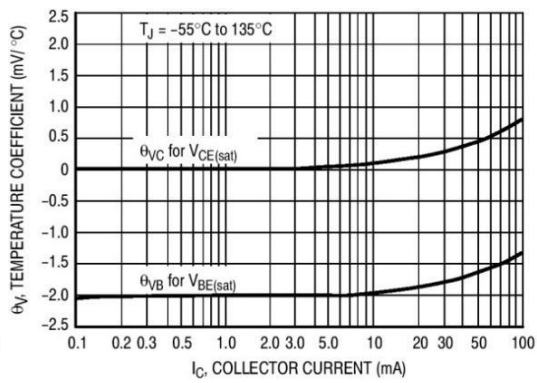
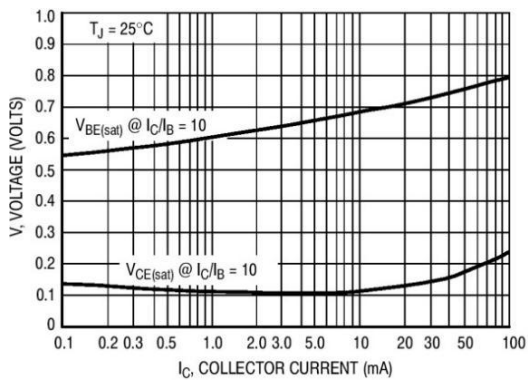
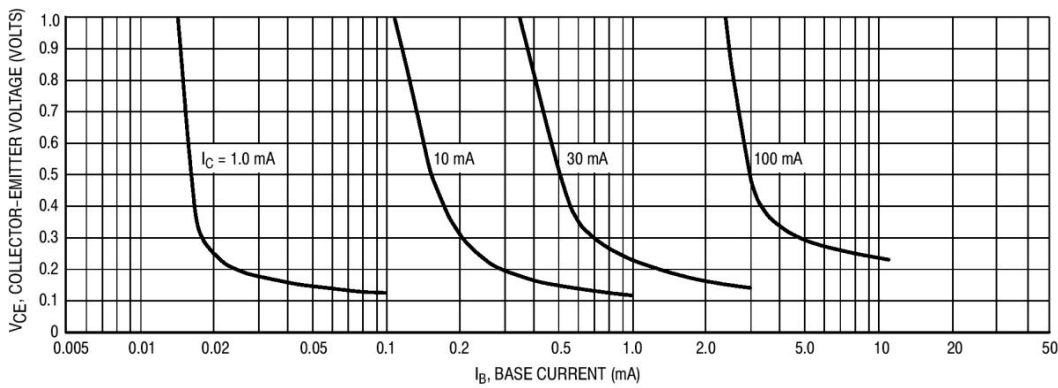
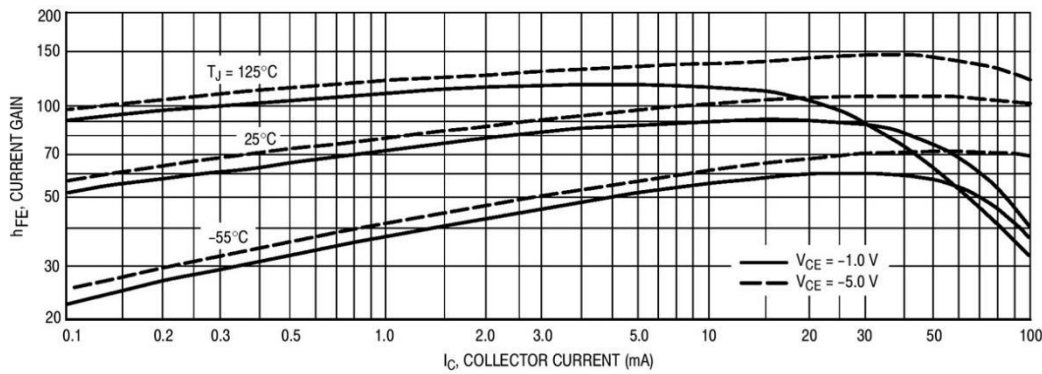
1. Transistor mounted on an FR-5 printed-circuit board.
ELECTRICAL CHARACTERISTICS 电特性

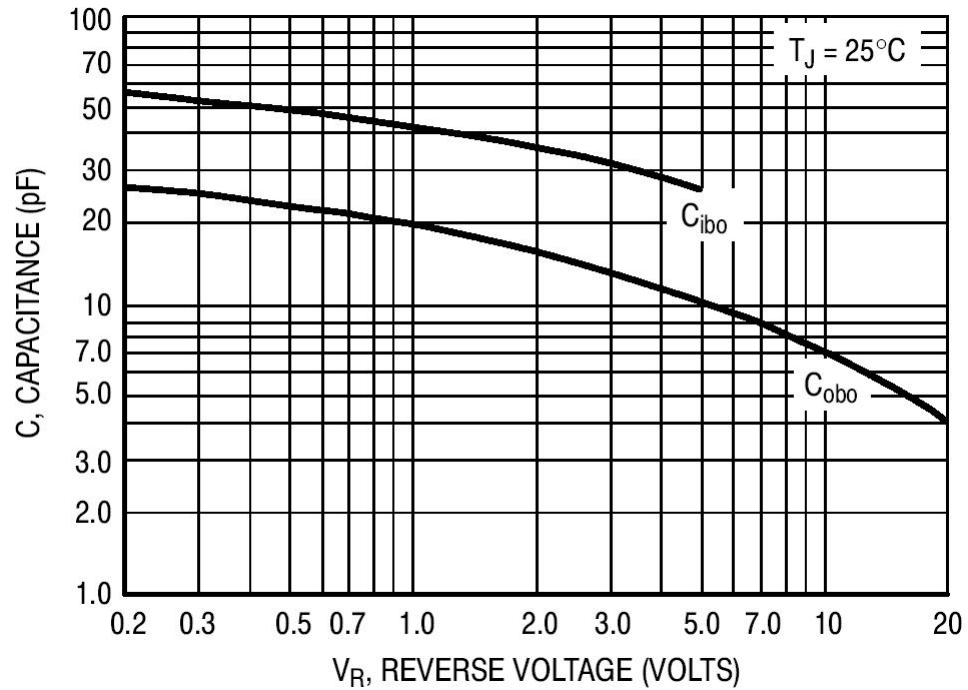
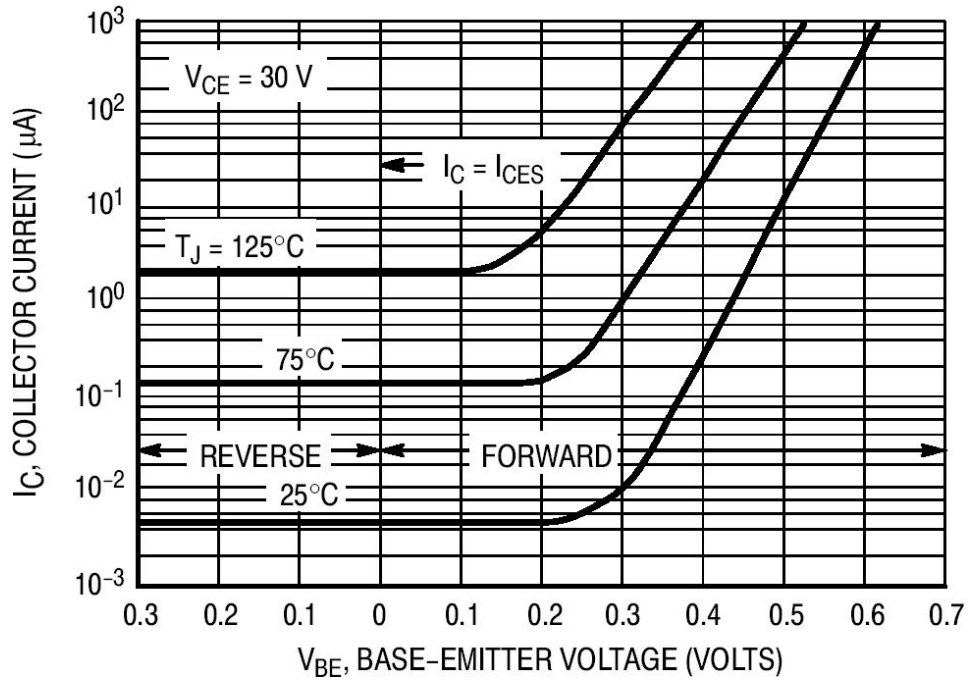
 (T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Test Condition 测试条件	Min 最小值	Max 最大值	Unit 单位
Collector cut-off current 集电极截止电流	I _{CBO}	V _{CB} = -120Vdc, I _E = 0	—	-50	nA
Emitter cut-off current 发射极截止电流	I _{EBO}	V _{EB} = -4.0Vdc, I _C = 0	—	-50	nA
Collector-Emitter Breakdown Voltage 集电极-发射极击穿电压	V _{(BR)CEO}	I _C = -1.0 mAdc, I _B = 0	-150	—	Vdc
Collector-Base Breakdown Voltage 集电极-基极击穿电压	V _{(BR)CBO}	I _C = -100μAdc, I _E = 0	-160	—	Vdc
Emitter-Base Breakdown Voltage 发射极-基极击穿电压	V _{(BR)EBO}	I _E = -10μAdc, I _C = 0	-5.0	—	Vdc
DC current gain 直流电流增益	h _{FE}	I _C = -1.0mAdc, V _{CE} = -5.0Vdc	50	—	—
		I _C = -10mAdc, V _{CE} = -5.0Vdc	100	300	—
		I _C = -50mAdc, V _{CE} = -5.0Vdc	50	—	—
Collector-emitter saturation voltage 集电极-发射极饱和压降	V _{CEsat}	I _C = -10mAdc, I _B = -1.0mAdc	—	-0.2	Vdc
		I _C = -50mAdc, I _B = -5.0mAdc	—	-0.5	Vdc

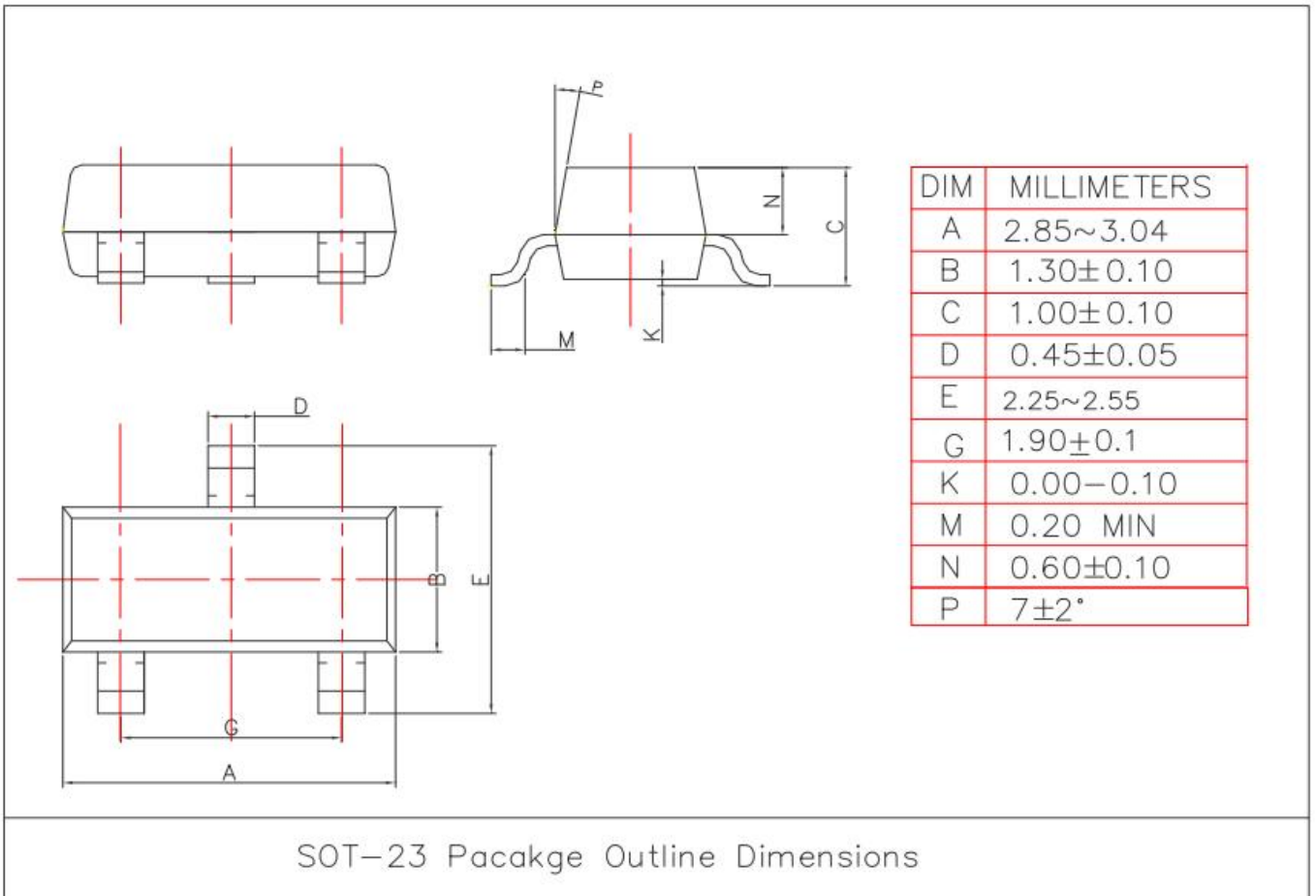
Base-Emitter Saturation Voltage 基极-发射极饱和压降	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$	—	-1.0	Vdc
		$I_C = -50\text{mA}, I_B = -5.0\text{mA}$	—	-1.0	Vdc
Transition Frequency 特征频率	f_T	$V_{CE} = -10\text{V}, I_E = -10\text{mA}, f = 100\text{MHz}$	100	300	MHz
Collector Output Capacitance 输出电容	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$	—	6	pF
Small-Signal Current Gain 小信号电流增益	h_{fe}	$V_{CE} = -10\text{Vdc}, I_C = -1.0\text{mA}$ $f = 1.0\text{KHz}$	40	200	—
Noise Figure 噪声系数	NF	$V_{CE} = -5.0\text{Vdc}, I_C = -250\mu\text{A}$ $R_g = 1.0\text{k}\Omega, f = 10\text{Hz} \sim 15.7\text{KHz}$	—	8.0	dB

Typical Performance Characteristics

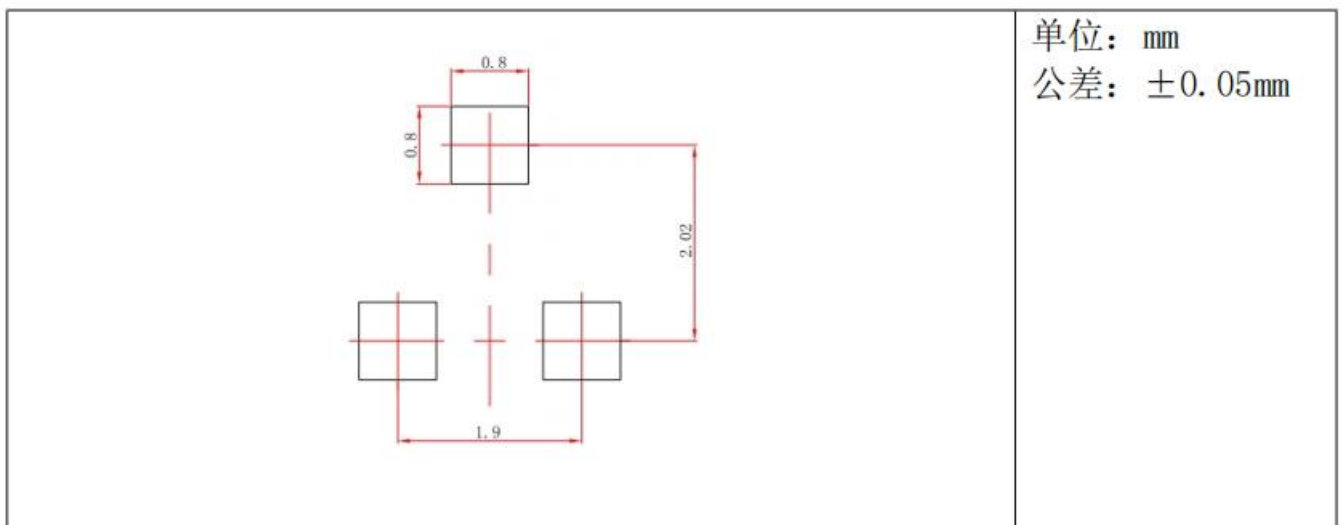




二、SOT-23 外形尺寸 (SOT-23 DIMENSION)

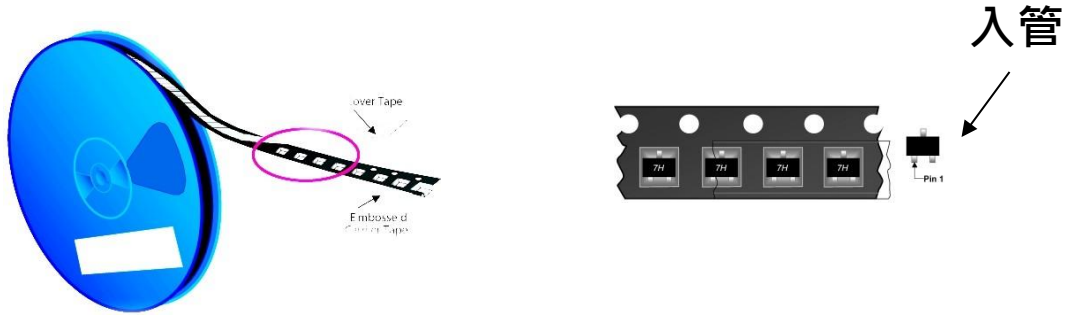


三、焊盘尺寸设计 SOT-23 Suggested Layout

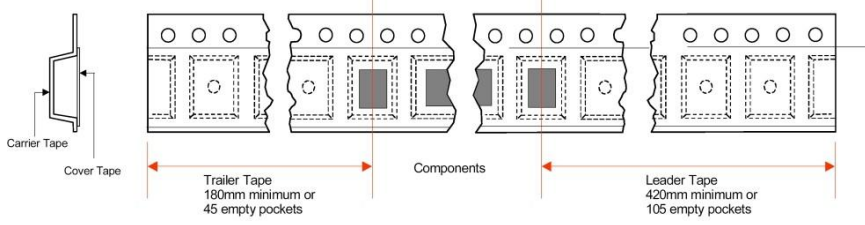


四、包装方式 Packings

封装形式	卷盘尺寸	只/卷	内盒尺寸	卷盘/内盒	只/内盒	外箱尺寸	内盒/外箱	只/外箱
SOT-23	7"	3000	190X190X135mm	10	30000	430 X 400 X 215mm	6	180K
			203X203X195mm	15	45000	440 X 440 X 230mm	4	180K



SOT-23 产品编带、包装图



SOT-23 带尾、带头空封数

